

ABSTRACT OF THE DISCLOSURE

Shift register electrodes are formed in an imaging area and a peripheral area through use of a single layer of conductive film, and a thick insulating film is deposited over those electrodes and planarized. The thick insulating film overlying the shift register electrodes in the peripheral area is kept as it is and on the other hand, the thick insulating film overlying the shift register electrodes is etched to just fill gaps between the shift register electrodes with the film, thereby allowing a light shielding metal layer overlying the shift register electrodes in the peripheral area and insulating films sandwiched therebetween to be formed without discontinuity. Since metal interconnect lines in the peripheral area have a thick and planarized insulating film formed thereunder, parasitic capacitance between diffusion layers/electrodes and the metal interconnect lines can be reduced, leading to reduction in power consumption of image sensor.